

## AMENDMENTS TO THE CLAIMS

Please cancel claims 18-20.

1. (Previously Presented) A process of growing a thin film of Al<sub>2</sub>O<sub>3</sub> on a substrate in a reaction chamber by a sequential vapor deposition process comprising a plurality of cycles, each cycle comprising:

exposing the substrate in the reaction chamber to gaseous trimethyl aluminum (TMA);

stopping provision of the gaseous TMA;

removing gaseous TMA from the reaction chamber;

exposing the substrate in the reaction chamber to atomic oxygen; and

removing atomic oxygen from the reaction chamber,

wherein in each cycle more than one monolayer of Al<sub>2</sub>O<sub>3</sub> is formed.

2. (Original) The process of claim 1, wherein in each cycle a layer of Al<sub>2</sub>O<sub>3</sub> 3 Å thick is formed.

3. (Previously Presented) The process of Claim 1, wherein the atomic oxygen is generated remotely in a radical generator.

4. (Original) The process of Claim 1, wherein the process is carried out at room temperature.

5. - 20. (Cancelled)